

## Index

### a

- active optical cable (AOC) 181
- arrayed waveguide grating (AWG) filter 150
- atomic-level processing 77
- Auger recombination process 303
- avalanche devices 167

### b

- band-engineered Ge-on-Si lasers 280
  - tensile strained Ge-on-Si 281
- band-engineered Ge-on-Si light emitters
  - electrically-pumped Ge-on-Si lasers 298
  - optical gain 294
  - optically-pumped Ge-on-Si lasers 297
  - spontaneous emission 289
- band-engineered Ge optical gain media
  - band gap narrowing 274
  - FCA losses 271
  - tensile strained Ge 269
  - tensile-strained  $N^+$  Ge 275
  - tensile strain with n-type doping 270
  - unstrained Ge 268
- band gap narrowing (BGN) 274
- band-to-band optical absorption, in bulk semiconductor materials 193
- bandwidth density 219
- Back-end-of-line (BEOL) 113
- Bipolar-Complementary Metal Oxide Semiconductors (BiCMOS)
  - flow 111
  - yield monitor behavior 105
- Binary decision diagram algorithm 219
- Bragg's law 53
- broad-band Quantum Confined Stark Effect (QCSE) effect 201
- bulk Ge
  - band structure of 267
  - photodetectors 165

- Burger's vector 58
- buried oxide 104
- butt-coupled Ge Electro-absorption (EAM), fabrication process 204
- butt-coupling approach 205, 212

### c

- carrier concentrations, in  $Si_{(1-x)}Ge_xC_y$  epitaxial films 83
- chemical mechanical polishing (CMP) 49, 60, 103, 204, 286
- chemical vapor deposition (CVD) 172, 173, 175
- CMOS-compatible materials 219
- Cobalt silicidation 116
- cocktail band engineering approach 277
- compressively-strained Ge layers 72
- conduction bands 222–224
- constant rate evanescent coupling regime 206
- critical thickness 234

### d

- defect density 66
  - and distribution, Ge layers 54
- deformation potential method/theory 222, 269, 274
- delta-doped Ge/P stacks 285
- delta doping, thermally activated drive-in diffusion 285
- dense wavelength division multiplexing (DWDM) 150
- depth profiles 91
- detectors
  - avalanche devices 167
  - bulk Ge photodetectors 165
  - chemical vapor deposition 172
  - device architectures 177

- detectors (*contd.*)
  - exfoliation 177
  - fiber-optics revolution 167
  - Ge condensation 175
  - Ge on Si 180
  - high-performance Ge detectors 169
  - historical background 165, 166
  - layer transfer technique 177
  - physical vapor deposition 170
  - process options and challenges 170
  - rapid melt growth 174
  - reliability 182, 183
  - Si-photonics 168
- diffusion doping, from spin-on-dopant (SOD) sources 286
- digital signal processing (DSP) 101
- dislocations 131
- dissociation energy 38
- dot layers, stacking of 237
- Drude model 273
- dry etching 240
- Dual Polarization Dual Quadrature (DPDQ) 180
- dynamic and active layers 155
  
- e**
- EAMs, *see* Electroabsorption modulators (EAMs)
- elastic compliance tensor 220
- elastic stiffness tensor 220
- electrical injection simulation, of  $n^+$  Si/ $n^+$ Ge/ $p^+$  Si double heterojunction structure 299
- electrically-pumped Ge-on-Si lasers 298
- electrical properties, c-GeOI substrates 69
- electroabsorption effect (EAE) 191
- electroabsorption modulators (EAMs) 191
- electron backscatter diffraction (EBSD) analysis 287, 288
- electron beam lithography (EBL) 155, 240
- electron-cyclotron resonance (ECR) plasma 155
- ellipsometry, GeSn alloy thin films 277
- enhanced light emission, Ge quantum dots 239
- epitaxial growth protocol and kinetics 50
- evanescent coupling 203
- evanescently coupled Ge EAM 206
- excimer laser deep ultraviolet (DUV) lithography 155
  
- f**
- Fabry–Perot (FP) cavity 250
- fast intervalley scattering process 302
  
- fiber optics
  - revolution 167
  - WDM in 220
- figure-of-merit (FOM) for EAM materials 193
- film mode matching method (FMM) 148
- finite difference time domain (FDTD) simulation 206
- flip-chip technology 108
- Franz–Keldysh effect (FKE)
  - absorption spectra 192
  - indirect gap 194
  - Kramers-Kronig relation 197
  - optical absorption process 192, 193
  - rigorous analysis 193
- Franz–Keldysh oscillations 192
- free carrier absorption (FCA) 272
- free electron absorption (FEA)
  - absorption curve 273
  - feature 273
  - from Drude model 273
- free hole absorption (FHA) 271
- front-end of line (FEOL) photonic-electronic integration 102
  
- g**
- GaAs
  - elastic stiffness constants 220
  - on Ge on Si 228
  - two dimensional strain vs. bandgap of 230
- Gas source MBE (GSMBE) 238, 239
- Ge-based photodetectors
  - Si-based modulation device 160
  - Si/silica-based wavelength filter 160
- Ge condensation
  - basic concept 123, 124
  - critical process parameters 125, 126
  - defects and dislocations 131
  - electrical properties 132
  - multi-gate and nanowire MOSFETs 138
  - photonic devices 139
  - planar GOI MOSFET 133
  - planar MOSFETs 135, 136
  - residual impurity 129
  - strain behavior 129, 130
  - stressor 139
  - thickness control 127
- Ge EAM
  - extinction ratio and insertion loss spectra 207
  - performance 207, 208
  - SEM photo 207, 210
- Ge-On-Insulator (GOI) 123
- geometric-parameter-dependence 245

- Ge QCSE modulators
    - butt-coupling scheme 205
    - extinction spectra 212, 213
    - operation wavelength 201, 202
    - side-entry approach 211
    - taper-lensed fibers 212
    - vs. Ge FKE 202
  - Ge quantum dots
    - advantages 233
    - enhanced light emission 239, 240
    - formation and luminescence 234
  - Ge quantum wells, crystallographic orientation 271
  - Ge<sub>0.97</sub>Si<sub>0.03</sub> race track ring modulator 210
  - germane 172
  - germanium (Ge)
    - elastic stiffness constants 220
    - net optical gain of 268
    - on Si beam 226
    - photo detector 114
  - GeSi EAM, performance 208
  - GeSi indirect gap 195
  - Ge surface passivation 55
  - Ge thin films, crystallographic orientation 271
- h**
- heat-treatment temperature
    - carrier concentration 83
    - dependence 90, 92
  - heterojunction bipolar transistors (HBTs) 168
  - high-numerical-aperture (NA) fiber 153
  - high-performance Ge detectors 169
  - high performance Ge quantum well structures 279
  - high-performance SiGe–C BiCMOS process 102
  - hole mobility 69
  - Hooke’s law 220
  - hut-clusters 235
  - hydrogen
    - complexes 34
    - crystalline Ge 25
    - defect 31
    - donor passivation 37
    - incorporation 26
    - interstitial 30
    - isolated 27
    - local vibrational mode 26
    - molecules 32
    - p-type Ge 40
  - hydrostatic deformation potential 222
- i**
- inductive coupled plasma 155
  - internal quantum efficiency (IQE) 301
  - interstitial H<sub>2</sub> 30
  - intervalley scattering absorption (IVSA) 273
  - inverse taper coupler 152, 153
  - island density 236
  - isolated hydrogen 27
- k**
- Kramers-Kronig relation 197
- l**
- laser sleeping 230
  - lateral PIN structure 255
  - lattice constant(s) 245
  - light emitters, strain engineering of 230
  - light extraction efficiency 246
  - liquid phase epitaxy (LPE) 281
  - local SOI technology 103
  - local SOI/WG 112
  - local vibrational mode (LVM) 26
  - low-energy plasma-enhanced CVD (LEPECVD) 174
  - low-pressure plasma etching 155
  - low temperature proton implantation 30
  - luminescence transition 235
- m**
- Mach–Zehnder depletion type modulators 111
  - Mach–Zehnder interferometer (MZI) 119
  - Mach–Zehnder interferometer structures 191
  - Mach–Zehnder modulators 110, 119
  - macroscopic strain state 65
  - metal oxide semiconductor field effect transistors (MOSFETs) 49
  - metal-semiconductor-metal (MSM) diodes 178
  - micro-electromechanical systems (MEMS) 282
  - microdisk 261
  - microdisk/ring
    - description 248
    - photoluminescence 249
  - micromachining-based suspension platform 283
  - microtwins 131
  - mode-converter butt-coupling design 204
  - modulator 113
  - modulator technology 108
  - molecular beam epitaxy (MBE) 274

- multi-gate and nanowire MOSFETs 138
- multi-mode interference (MMI) couplers 205
- multiple QW (MQW) structure 200
- muon spin research ( $\mu$ SR) 28
- muonium (Mu) 29
  
- n**
- nanorib waveguides 107
- nanostrip waveguides 106
- near-future laser integration 108
- no-phonon line 234
- $n^+$  Si/ $n^+$  Ge/ $p^+$  Si Double Hetero (DH) structure 299
- n-type doping
  - *in-situ* doping 285
  - delta doping 285
  - diffusion doping, from SOD sources 286
  - *in-situ* doping 284
  - solubility, of n-type dopants 282
  
- o**
- on-chip optical interconnection 233
- optical bleaching, of direct gap absorption 268
- optical frequency-domain reflectometry 107
- optical gain 294
- optical interconnect technology 233
- optically-pumped Ge-on-Si lasers 297
- optical pumping 240
- optical waveguides 59
- overcladding 156
  
- p**
- passive silicon waveguide technology 105
- $\gamma$ – $\gamma$  perturbed angular correlation (PAC) 36
- phase shifter efficiency 109
- PH<sub>3</sub> exposure temperature dependence 89
- photocurrent ratio measurement 212
- photo-detectors (PD) 59, 113
- photoluminescence (PL)
  - double-heterostructure PhC nanocavities 247
  - from direct Ge band gap transition 268
  - L3-type Photonic Crystal (PhC) nanocavities 242
  - photonic crystal cavity 241
  - spectra, Ge on Si beam 228
- photonic crystal cavity
  - description 240
  - photoluminescence 241
- photonic devices 139
- photonic–electronic integration 101
- 3D photonic integration 287
- photonic integrated circuits (PICs) 106
- photonic SOI wafers 103
- photonic wire waveguide 148
- photoreflectance, GeSn alloy thin films 277
- physical vapor deposition (PVD) 170, 171
- planar GOI MOSFET 133
- planar MOSFETs 135, 136
- plane-wave expansion (PWE) 243
- plasma-enhanced chemical vapor deposition (PE-CVD) 156, 281
- polarization mode dispersion 151
- proton implantation 27
- pseudomorphic Si<sub>1-x</sub>Ge<sub>x</sub>, conduction and valence band offsets 199
- Purcell effect 239
  
- q**
- Quality (Q) factor 244, 245, 294
- quadrature-amplitude modulation (QAM) 110
- quadrature-phase shift keying (QPSK) 110
- quantum-confined stark effect (QCSE)
  - vs. FKE 197
  - quantitative modeling 199
  - tensile strain engineering 200
- quantum confinement effect 234
- QW structures, band diagrams and wavefunctions 198
  
- r**
- Radio Frequency (RF) phase-shifter electrodes 111
- Raman shift 96
- rapid melt growth (RMG) 174, 176, 281
- rapid thermal annealing (RTA) 281, 286
- reactive ion etching 293
- reciprocal space mapping 68
- reduced pressure chemical vapor deposition (RP-CVD) 156
- refractive index 106, 150
- remote hydrogen plasma 27
- resistive metal interconnect 233
- rib-type waveguides 148
- RIB WG/coupler 113
- rotation matrix 221
  
- s**
- scanning electron microscopy (SEM), Si beam structure 224
- scattering loss 151
- Schottky contacts 43
- self-limited reaction, of hydride 85
- Sentaurus 108, 109
- separate electron barrier approach 280
- sheer strain deformation potential 222

- Si electro-optical (EO) modulators 191
  - SiGe alloy dots 236
  - Si<sub>1-x</sub>Ge<sub>x</sub> epitaxial growth
    - atomic-layer doping 84
    - *in situ* doping characteristics 78, 81, 82
    - boron atomic-layer doping 85, 88
    - carrier and impurity concentration 82, 84
    - phosphorous atomic-layer doping 88, 89, 91–93
  - Si/Ge heterojunctions 179
  - SiGe-On-Insulator (SGOI) layer 123
  - Si<sub>0.15</sub>Ge<sub>0.85</sub> process flow 62
  - Si passivation process 50
  - Si-photonics 168
  - Si/Si<sub>1-x</sub>Ge<sub>x</sub>/Si heterostructure growth, process sequence 78
  - Si/Si<sub>1-x</sub>Ge<sub>x</sub>/Si(100) structure, carbon atomic-layer doping 94, 95
  - Si waveguide core 155
  - silane 172
  - silicon (Si)
    - bandgap vs. strain 224
    - beam fabrication 224
    - beam structure, SEM image of 224
    - cantilever structure, strain distribution in 224
    - elastic stiffness constants 220
    - epitaxy 103
    - nanowaveguides 107
    - photoluminescence spectra 225
  - silicon-based light emitter technology 233
  - silicon-on-insulator (SOI) 103
  - silicon-on-insulator (SOI) substrates 59
  - silicon oxy-nitride (SiON) 156
  - silicon photonics 101, 233
  - silicon photonic wire waveguiding system
    - external coupling 152
    - Ge photonic devices 153
    - guided modes 148, 149
  - silicon-rich silica (SiO<sub>x</sub>) 156
  - SIMS depth profile 93
  - single-mode-fiber (SMF) 106
  - Smart-cut® technique 32
  - Sn alloying 277, 278, 287
  - SOD sources, *see* spin-on dopant (SOD) sources
  - SOI strip waveguides 105
  - solubility, of n-type dopants 282
  - spin-on dopant (SOD) sources 286
  - spin-orbit interaction 222
  - spontaneous emission 289
  - spontaneous emission rate (SER), of light emitters 239
  - spot-size converter (SSC) 152, 156
  - standard semiconductor device simulators 108
  - standing wave type resonator 233
  - strain state 52
  - strain-tunable light emitter 230
  - Stranski–Krastanov growth 280, 286
  - Stranski–Krastanow growth mode 58
  - stress 221
  - stressors 139
  - structural properties, c-GeOI substrates 68
  - surface and film morphology 57
  - surface morphology 51, 64
- t**
- tapered mode converters 204
  - tapered mode coupler, for waveguide coupling 206
  - 10 Gbit/sec modulator with driver 118
  - tensile strain
    - engineering 200, 277
    - with n-type doping 270
  - tensile strained Ge 269
  - tensile strained Ge-on-Si 281
  - tensile strained Ge-on-Si, absorption spectra of 196
  - tensile-strained n<sup>+</sup> Ge 275
  - thermal expansion coefficients 53
  - thermally activated drive-in diffusion, delta doping 285
  - thermally-expanded-core (TEC) technology 153
  - thick, fully relaxed Ge(001) layers 73
  - threading dislocation density (TDD) 115
  - 3-dB multimode interference (MMI) tap coupler 160
  - Three dimensional (3D) finite-difference time-domain (FDTD) methods 243
  - threshold voltage 69
  - total internal reflection (TIR) 240
  - transimpedance amplifier (TIA) 178
  - transmission spectra, of unpackaged
    - 10-channel device 210, 211
  - traveling wave type resonator 233
  - 28Gbit/sec transmitters 120
  - two-dimensional (2D) photonic crystal (PhC) cavity 240
  - two dimensional strain vs. bandgap, of GaAs 230
- u**
- ultrahigh vacuum chemical vapor deposition (UHV-CVD) 156
  - unpackaged 10-channel device, transmission spectra 210, 211

**v**

valence bands 222, 223  
variable optical attenuators (VOAs) 160  
Vegard's law 82  
vertical PIN structure 252

**w**

wafer map 117  
waveguide-coupled GeSi EAM 205  
waveguide coupling 203  
waveguide-integrated Ge QCSE modulator,  
device structure 213

waveguide propagation performance  
158

wavelength division multiplexing (WDM)  
160, 219

wet chemical etching 27

whispering gallery mode (WGM) resonators  
240

**x**

X-ray diffraction (XRD) 52